

## A 12 V, 15 m $\Omega,$ 4 A Load Switch with $V_{IN}$ Lockout Select and Power Good Output

#### **General Description**

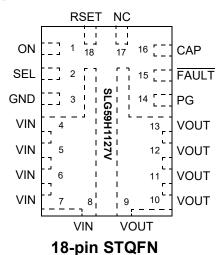
The SLG59H1127V is a high-performance, self-powered 15 m $\Omega$  nFET load switch designed for all 4.5 V to 12 V power rails up to 4 A. Using a proprietary MOSFET design, the SLG59H1127V achieves a stable 15 m $\Omega$  RDS<sub>ON</sub> across a wide input voltage range. In combining novel FET design and copper pillar interconnects, the SLG59H1127V package also exhibits a low thermal resistance for high-current operation.

Designed to operate over a -40 °C to 85 °C range, the SLG59H1127V is available in a low thermal resistance, RoHS-compliant,  $1.6 \times 3.0 \text{ mm}$  STQFN package.

#### **Features**

- Wide Operating Input Voltage: 4.5 V to 13.2 V
- Maximum Continuous Current: 4 A
- Automatic nFET SOA Protection
  5 W SOA Protection Threshold
- High-performance MOSFET Switch Low RDS<sub>ON</sub>: 15 m $\Omega$  at V<sub>IN</sub> = 12 V Low  $\Delta$ RDS<sub>ON</sub>/ $\Delta$ V<sub>IN</sub>: < 0.05 m $\Omega$ /V Low  $\Delta$ RDS<sub>ON</sub>/ $\Delta$ T: < 0.06 m $\Omega$ /°C
- Capacitor-adjustable Inrush Current Control
- Two stage Current Limit Protection: Resistor-adjustable Active Current Limit Internal Short-circuit Current limit
- Open-drain Power Good (PG) Signaling
- Open-drain FAULT Signaling
- Fast 4 kΩ Output Discharge
- · Pb-Free / Halogen-Free / RoHS Compliant Packaging

#### **Pin Configuration**

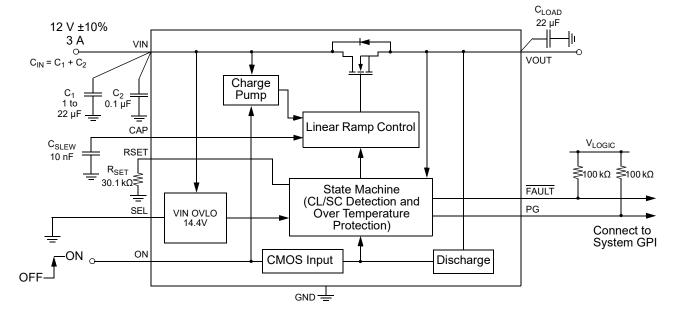


1.6 x 3.0 mm, 0.40mm pitch

(Top View)

#### Applications

- Enterprise Computing & Telecom Equipment 5 V and 12 V Point-of-Load Power Distribution
- PCI/PCIe Adapter Cards
- General-purpose High-voltage, Power-Rail Switching
- Multifunction Printers
- Fan Motor Control



#### **Block Diagram**

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# A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### **Pin Description**

Pin #	Pin Name	Туре	Pin Description
1	ON	Input	A low-to-high transition on this pin initiates the operation of the SLG59H1127V's state machine. ON is an asserted HIGH, level-sensitive CMOS input with ON_V <sub>IL</sub> < 0.3 V and ON_V <sub>IH</sub> > 0.9 V. As the ON pin input circuit does not have an internal pull-down resistor, connect this pin to a general-purpose output (GPO) of a microcontroller, an application processor, or a system controller – do not allow this pin to be open-circuited.
2	SEL	Input	Connect this pin to GND.
3	GND	GND	Pin 3 is the main ground connection for the SLG59H1127V's internal charge pump, its gate driver and current-limit circuits as well as its internal state machine. Therefore, use a short, stout connection from Pin 3 to the system's analog or power plane.
4-8	VIN	MOSFET	VIN supplies the power for the operation of the SLG59H1127V, its internal control circuitry, and the drain terminal of the nFET load switch. With 5 pins fused together at VIN, connect a 22 $\mu$ F (or larger) low-ESR capacitor from this pin to ground. Capacitors used at VIN should be rated at 20 V or higher.
9-13	VOUT	MOSFET	Source terminal of n-channel MOSFET (5 pins fused for VOUT). Connect a 22 $\mu$ F (or larger) low-ESR capacitor from this pin to ground. Capacitors used at VOUT should be rated at 20 V or higher.
14	PG	Output	An open-drain output, PG is asserted within TPG <sub>HIGH</sub> when V <sub>OUT</sub> is higher than the SLG59H1127V's PG <sub>TRIGGER</sub> threshold. PG output becomes deasserted within TPG <sub>LOW</sub> when V <sub>OUT</sub> is less than the PG <sub>HYS</sub> threshold. PG is not defined for V <sub>IN</sub> < 4 V.
15	FAULT	Output	An open-drain output, FAULT is asserted within TFAULT <sub>LOW</sub> when a V <sub>IN</sub> overvoltage, a current-limit, or an over-temperature condition is detected. FAULT is deasserted within TFAULT <sub>HIGH</sub> when the fault condition is removed. Connect an 100 k $\Omega$ external resistor from the FAULT pin to local system logic supply.
16	САР	Output	A low-ESR, stable dielectric, ceramic surface-mount capacitor connected from CAP pin to GND sets the V <sub>OUT</sub> slew rate and overall turn-on time of the SLG59H1127V. For best performance, the range for C <sub>SLEW</sub> values are 10 nF $\leq$ C <sub>SLEW</sub> $\leq$ 20 nF – please see typical characteristics for additional information. Capacitors used at the CAP pin should be rated at 10 V or higher. Please consult Applications Section on how to select C <sub>SLEW</sub> based on V <sub>OUT</sub> slew rate and loading conditions.
17	NC	NC	No Connect
18	RSET	Input	A 1%-tolerance, metal-film resistor between 18 k $\Omega$ and 91 k $\Omega$ sets the SLG59H1127V's active current limit. A 91 k $\Omega$ resistor sets the SLG59H1127V's active current limit to 1 A and a 18 k $\Omega$ resistor sets the active current limit to 5 A.

#### **Ordering Information**

Part Number	Туре	Production Flow
SLG59H1127V	STQFN 18L FC	Industrial, -40 °C to 85 °C
SLG59H1127VTR	STQFN 18L FC (Tape and Reel)	Industrial, -40 °C to 85 °C

Datasheet	Revision 1.03	
CEB0011-120-01	Page 2 of 32	

## A 12 V, 15 m $\Omega,$ 4 A Load Switch with $V_{IN}$ Lockout Select and Power Good Output

#### **Absolute Maximum Ratings**

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
	Lead Switch Innut Valtana to CND	Continuous	-0.3		16	V
V <sub>IN</sub> to GND	Load Switch Input Voltage to GND	Maximum pulsed V <sub>IN</sub> , pulse width < 0.1 s			18	V
V <sub>OUT</sub> to GND	Load Switch Output Voltage to GND		-0.3		V <sub>IN</sub>	V
ON, SEL, CAP, RSET, PG, and FAULT to GND	ON, SEL, CAP, RSET, PG, and FAULT Pin Voltages to GND		-0.3		7	V
Τ <sub>S</sub>	Storage Temperature		-65		150	°C
ESD <sub>HBM</sub>	ESD Protection	Human Body Model	2000			V
ESD <sub>CDM</sub>	ESD Protection	Charged Device Model	500		-	V
MSL	Moisture Sensitivity Level			1		
		Determined using 1 in <sup>2</sup> , 1 oz. copper pads under each VIN and VOUT terminal and FR4 pcb material.		40		°C/W
$\theta_{JA}$	Thermal Resistance; 1.6 x 3.0 mm 18L STQFN	Determined using 0.25 in <sup>2</sup> , 1 oz. copper pads under each VIN and VOUT terminal and FR4 pcb material.		77		°C/W
		Determined using 0.008 in <sup>2</sup> , 1 oz. copper pads under each VIN and VOUT terminal and FR4 pcb material.		125		°C/W
MOSFET IDS <sub>CONT</sub>	Continuous Current from VIN to VOUT	T <sub>J</sub> < 150 °C			4	А
MOSFET IDS <sub>PEAK</sub>	Peak Current from VIN to VOUT	Maximum pulsed switch current, pulse width < 1 ms			6	А

Note: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

#### **Electrical Characteristics**

 $4.5 \text{ V} \le \text{V}_{\text{IN}} \le 13.2 \text{ V}$ ;  $C_{\text{IN}} = 22 \text{ }\mu\text{F}$ ,  $T_{\text{A}} = -40 \text{ }^{\circ}\text{C}$  to 85  $^{\circ}\text{C}$ , unless otherwise noted. Typical values are at  $T_{\text{A}} = 25 \text{ }^{\circ}\text{C}$ 

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
V <sub>IN</sub>	Operating Input Voltage		4.5		13.2	V
V <sub>IN(OVLO)</sub>	V <sub>IN</sub> Overvoltage Lockout Threshold	V <sub>IN</sub> ↑; SEL= 0	13.5	14.4	15.2	V
V <sub>IN(OVLOHYST)</sub>	V <sub>IN</sub> Overvoltage Lockout Hysteresis			2		%
V <sub>IN(UVLO)</sub>	V <sub>IN</sub> Undervoltage Lockout Threshold	V <sub>IN</sub> ↓	2.4		3.8	V
Ι <sub>Q</sub>	Quiescent Supply Current	ON = HIGH; I <sub>DS</sub> = 0 A		0.5	0.6	mA
I <sub>SHDN</sub>	OFF Mode Supply Current	ON = LOW; I <sub>DS</sub> = 0 A		1	3	μA
RDS <sub>ON</sub>	ON Resistance	T <sub>A</sub> = 25°C; I <sub>DS</sub> = 0.1 A		15	18	mΩ
ND3ON		T <sub>A</sub> = 85°C; I <sub>DS</sub> = 0.1 A		22	24	mΩ
MOSFET IDS	Current from VIN to VOUT	Continuous			4	А

# A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### **Electrical Characteristics (continued)**

 $4.5 \text{ V} \le \text{V}_{\text{IN}} \le 13.2 \text{ V}$ ;  $C_{\text{IN}} = 22 \ \mu\text{F}$ ,  $T_{\text{A}} = -40 \ ^{\circ}\text{C}$  to 85  $^{\circ}\text{C}$ , unless otherwise noted. Typical values are at  $T_{\text{A}} = 25 \ ^{\circ}\text{C}$ 

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
	Active Current Limit, IACL	V <sub>OUT</sub> > 0.5 V; R <sub>SET</sub> = 30.1 kΩ	2.8	3.2	3.6	Α
I <sub>LIMIT</sub>	Short-circuit Current Limit, I <sub>SCL</sub>	V <sub>OUT</sub> < 0.5 V		0.5		Α
T <sub>ACL</sub>	Active Current Limit Response Time			120		μs
R <sub>DISCHRG</sub>	Output Discharge Resistance		3.5	4.4	5.3	kΩ
C <sub>LOAD</sub>	Output Load Capacitance	C <sub>LOAD</sub> connected from VOUT to GND		22		μF
Tours	ON Delay Time	50% ON to 10% V <sub>OUT</sub> ↑; V <sub>IN</sub> = 4.5 V; C <sub>SLEW</sub> = 10 nF; R <sub>LOAD</sub> = 100 Ω, C <sub>LOAD</sub> = 10 μF		0.4	0.5	ms
T <sub>ON_</sub> Delay		50% ON to 10% V <sub>OUT</sub> ↑; V <sub>IN</sub> = 12 V; C <sub>SLEW</sub> = 10 nF; R <sub>LOAD</sub> = 100 Ω, C <sub>LOAD</sub> = 10µF		0.7	0.9	ms
		50% ON to 90% V <sub>OUT</sub> $\uparrow$	Set by I	External	C <sub>SLEW</sub> <sup>1</sup>	ms
T <sub>Total_ON</sub>	Total Turn ON Time	50% ON to 90% V <sub>OUT</sub> ↑; V <sub>IN</sub> = 4.5 V; C <sub>SLEW</sub> = 10 nF; R <sub>LOAD</sub> = 100 Ω, C <sub>LOAD</sub> = 10 μF		1.6	2.1	ms
_		50% ON to 90% V <sub>OUT</sub> ↑; V <sub>IN</sub> = 12 V; C <sub>SLEW</sub> = 10 nF; R <sub>LOAD</sub> = 100 Ω, C <sub>LOAD</sub> = 10 μF		4	6	ms
		10% V <sub>OUT</sub> to 90% V <sub>OUT</sub> ↑	Set by I	External	C <sub>SLEW</sub> <sup>1</sup>	V/ms
V <sub>OUT(SR)</sub>	V <sub>OUT</sub> Slew rate	10% V <sub>OUT</sub> to 90% V <sub>OUT</sub> $\uparrow$ ; V <sub>IN</sub> = 4.5 V to 12 V; C <sub>SLEW</sub> = 10 nF; R <sub>LOAD</sub> = 100 Ω, C <sub>LOAD</sub> = 10 μF	2.7	3.2	3.9	V/ms
T <sub>OFF_Delay</sub>	OFF Delay Time	50% ON to V <sub>OUT</sub> Fall Start ↓; V <sub>IN</sub> = 4.5 V to 12 V; R <sub>LOAD</sub> = 100 Ω, No C <sub>LOAD</sub>		15		μs
T <sub>FALL</sub>	V <sub>OUT</sub> Fall Time	90% V <sub>OUT</sub> ↓ to 10% V <sub>OUT</sub> ↓ V <sub>IN</sub> = 4.5 V to 12 V; R <sub>LOAD</sub> = 100 Ω, No C <sub>LOAD</sub>	10.4	12.7	25	μs
TFAULT <sub>LOW</sub>	FAULT Assertion Time	Abnormal Step Load Current event to Fault↓ $I_{ACL}$ = 1 A; $V_{IN}$ = 12 V; $R_{SET}$ = 91 kΩ; switch in 10 Ω load;		80		μs
TFAULT <sub>HIGH</sub>	FAULT De-assertion Time	Delay to FAULT↑ after fault condition is removed; I <sub>ACL</sub> = 1 A; V <sub>IN</sub> = 12 V; R <sub>SET</sub> = 91 kΩ; switch out 10 Ω load		180		μs
FAULT <sub>VOL</sub>	FAULT Output Low Voltage	I <sub>FAULT</sub> = 1 mA		0.2		V
V <sub>PG(OL)</sub>	PG Pin Output Low Voltage	$V_{LOGIC}$ = 5 V, $I_{PG(OL)}$ = -0.1 mA			0.4	V
V <sub>PG(OH)</sub>	PG Pin Output High Voltage	V <sub>LOGIC</sub> = 5 V, I <sub>PG(OH)</sub> = 0.1 mA	V <sub>LOGIC</sub> - 0.4		V <sub>LOGIC</sub>	V
PG <sub>TRIGGER</sub>	Power Good Threshold Voltage Level	V <sub>OUT</sub> % of V <sub>IN</sub>	86	90	94	%

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# A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### **Electrical Characteristics (continued)**

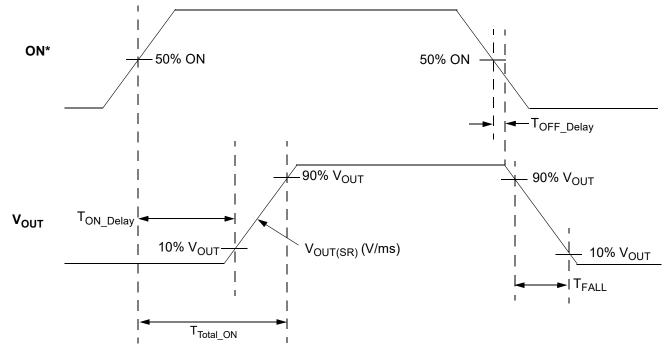
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Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
PG <sub>HYS</sub>	Power Good Hysteresis ↓	$V_{OUT} \downarrow \%$ of $V_{IN}$	81	85	89	%
TPG <sub>HIGH</sub>	PG Assertion Time	Delay to PG↑ after PG <sub>TRIGGER</sub> threshold is crossed.	1	1.25	1.5	ms
TPG <sub>LOW</sub>	PG De-assertion Time	Delay to PG↓ after PG <sub>TRIGGER</sub> threshold is crossed.		7		μs
ON_V <sub>IH</sub>	ON Pin Input High Voltage		0.9		5	V
ON_V <sub>IL</sub>	ON Pin Input Low Voltage		-0.3	0	0.3	V
I <sub>ON(Leakage)</sub>	ON Pin Leakage Current	$1 \text{ V} \le \text{ON} \le 5 \text{ V} \text{ or ON} = \text{GND}$			1	μA
THERMON	Thermal Protection Shutdown Threshold			125		°C
THERMOFF	Thermal Protection Restart Threshold			100		°C
Notes: 1. Refer to typical	Notes: 1. Refer to typical Timing Parameter vs. C <sub>SLEW</sub> performance charts for additional information when available.					

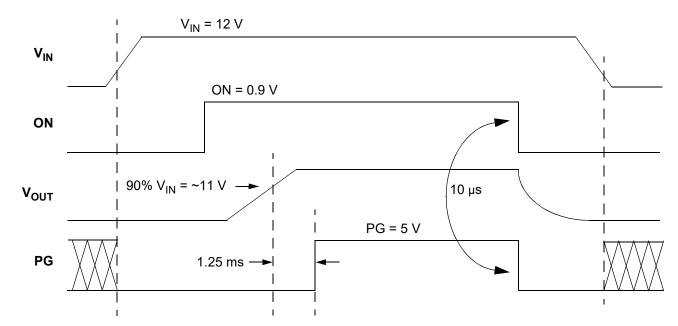


A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

## T<sub>Total\_ON</sub>, T<sub>ON\_Delay</sub> and Slew Rate Measurement Timing Details



\* Rise and Fall times of the ON signal are 100 ns



#### **PG Timing Details**

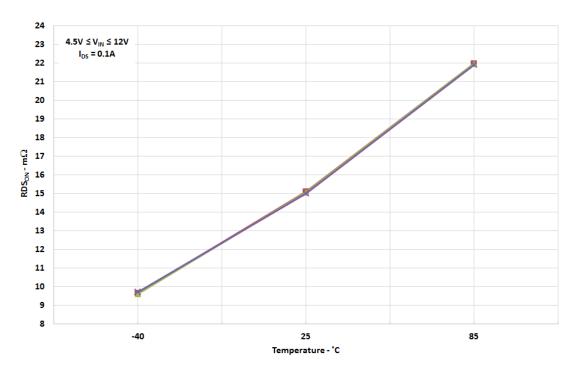
Datasheet	Revision 1.03	2-Feb-2022
CFR0011-120-01	Page 6 of 32	©2022 Renesas Electronics Corporation



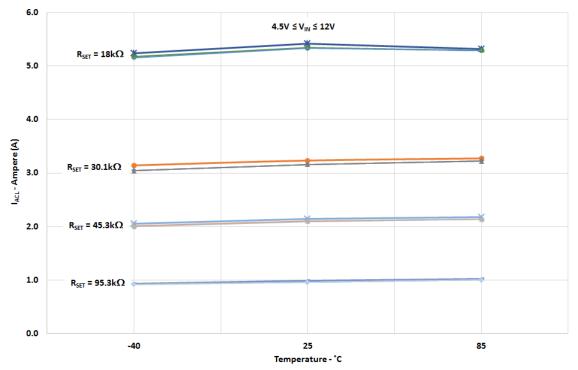
# A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### **Typical Performance Characteristics**

#### $\mathsf{RDS}_\mathsf{ON}$ vs. Temperature and $\mathsf{V}_\mathsf{IN}$



#### $I_{ACL}$ vs. Temperature, $R_{SET},$ and $V_{IN}$

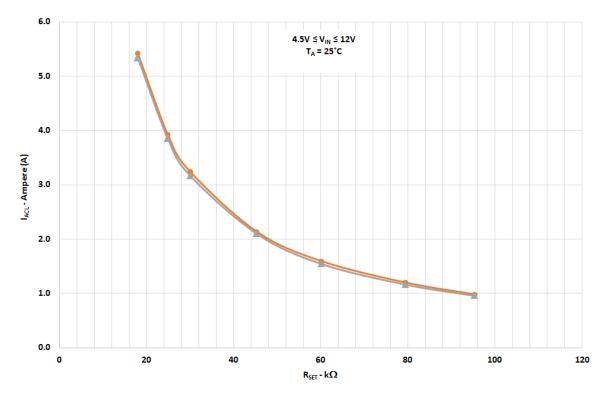


Datasheet	Revision 1.03	2-Feb-2022
	Page 7 of 32	

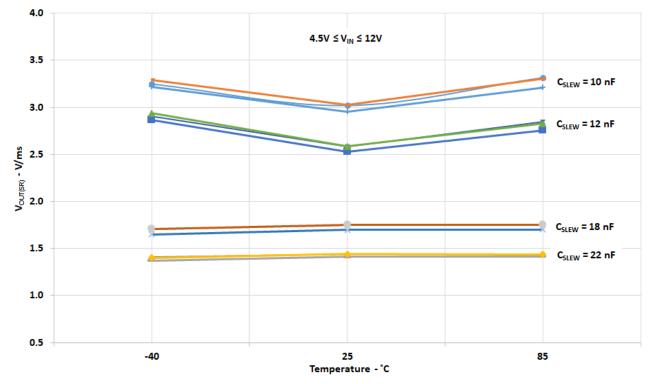


## A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### $I_{ACL}$ vs. $R_{SET},$ and $V_{IN}$



 $V_{\text{OUT}}$  Slew Rate vs. Temperature,  $V_{\text{IN}}$  , and  $C_{\text{SLEW}}$ 

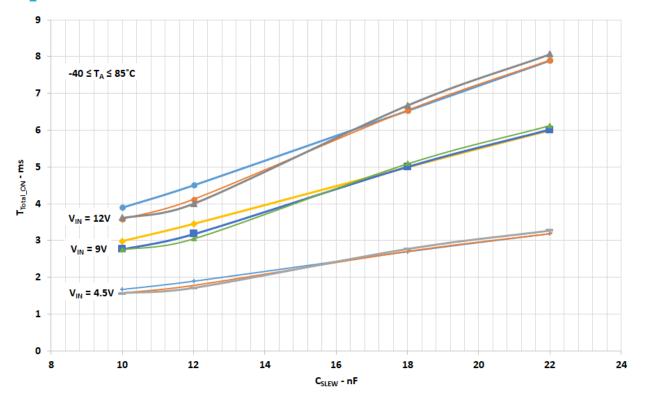


Datasheet	Revision 1.03	2-Feb-2022
CFR0011-120-01	Page 8 of 32	©2022 Renesas Electronics Corporation



# A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

### $T_{Total\_ON}$ vs. $C_{SLEW},$ $V_{IN},$ and Temperature

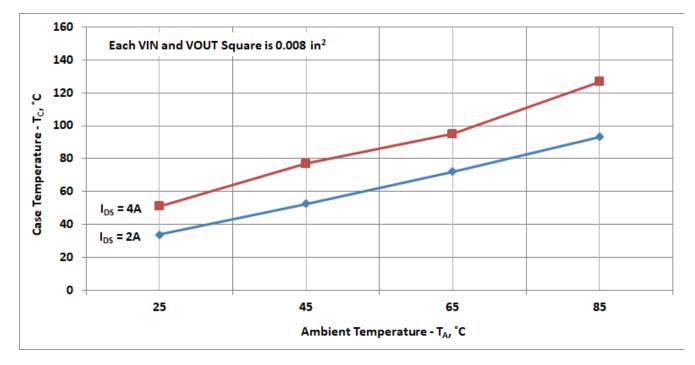




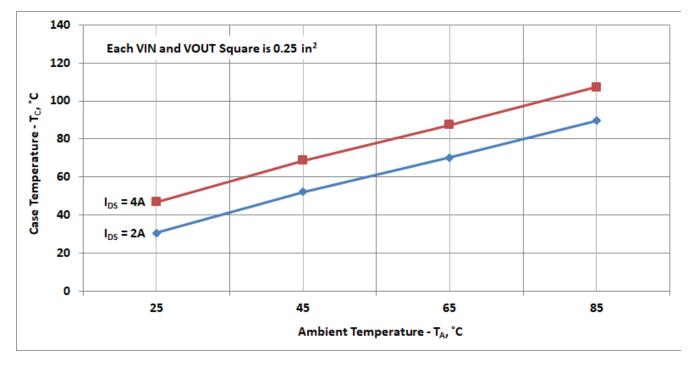
## A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### **Case Measurement**

## Case Temperature vs. Ambient Temperature (each VIN and VOUT square is 0.008 in<sup>2</sup>, no airflow)



#### Case Temperature vs. Ambient Temperature (each VIN and VOUT square is 0.25 in<sup>2</sup>, no airflow)

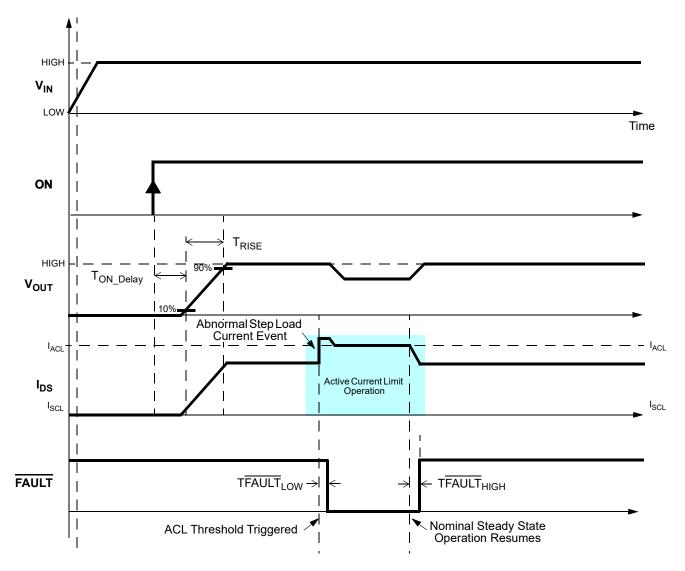


Datasheet	Revision 1.03



A 12 V, 15 m $\Omega,$  4 A Load Switch with  $V_{IN}$  Lockout Select and Power Good Output

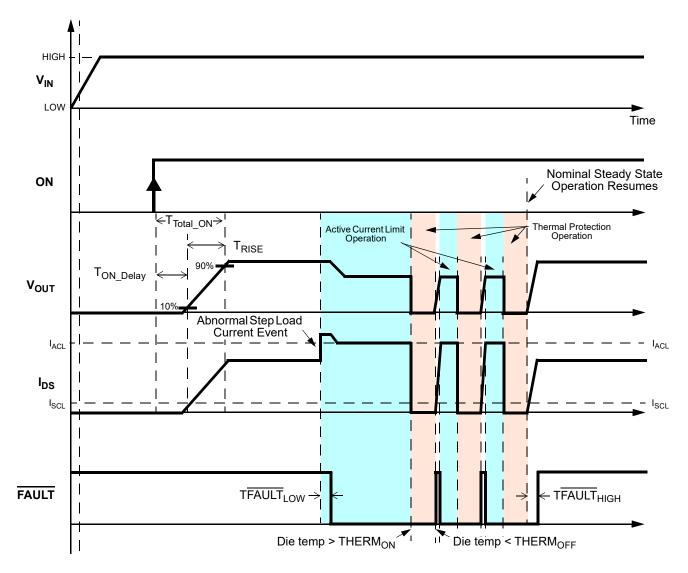
#### **Timing Diagram - Basic Operation including Active Current Limit Protection**





A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### **Timing Diagram - Active Current Limit & Thermal Protection Operation**



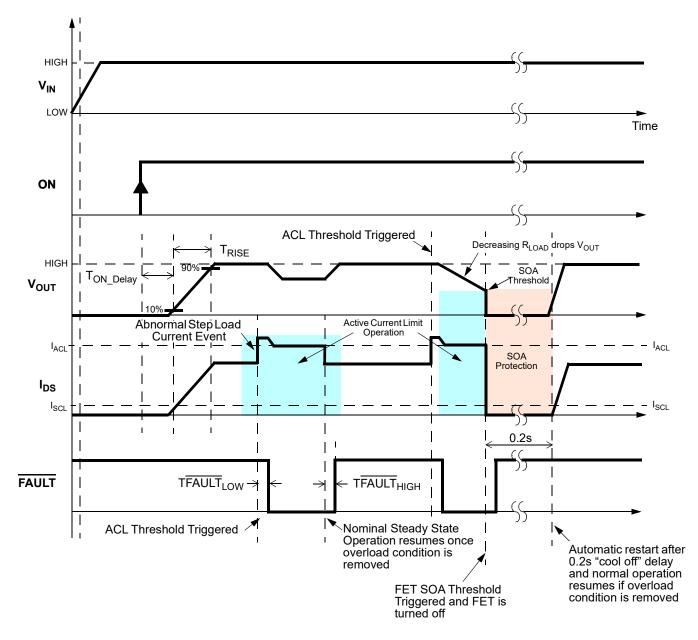
Datasheet	Revision 1.03
	Dage 10 of 20

## RENESAS

### SLG59H1127V

A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### Timing Diagram - Basic Operation including Active Current + Internal FET SOA Protection





A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### SLG59H1127V Application Diagram

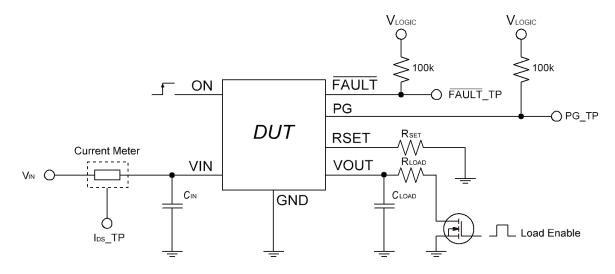


Figure 1. Test setup Application Diagram

#### **Typical Turn-on Waveforms**

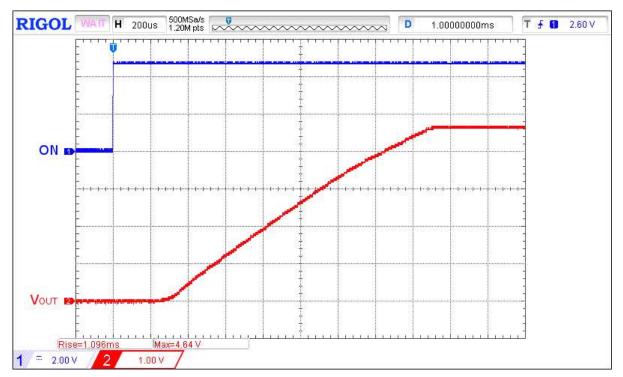


Figure 2. Typical Turn ON operation waveform for V<sub>IN</sub> = 4.5 V, C<sub>SLEW</sub> = 10 nF, C<sub>LOAD</sub> = 10  $\mu$ F, R<sub>LOAD</sub> = 100  $\Omega$ 



A 12 V, 15 m $\Omega,$  4 A Load Switch with  $V_{IN}$  Lockout Select and Power Good Output

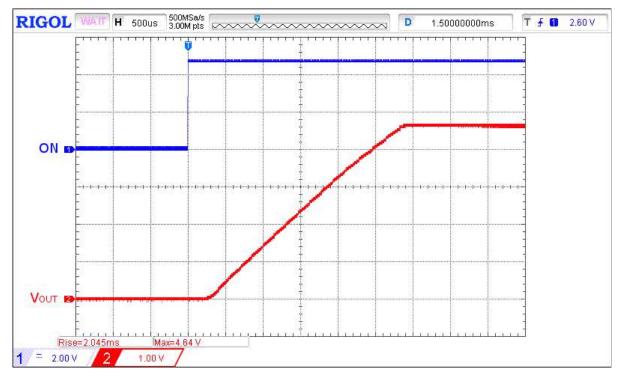


Figure 3. Typical Turn ON operation waveform for V<sub>IN</sub> = 4.5 V, C<sub>SLEW</sub> = 18 nF, C<sub>LOAD</sub> = 10  $\mu$ F, R<sub>LOAD</sub> = 100  $\Omega$ 

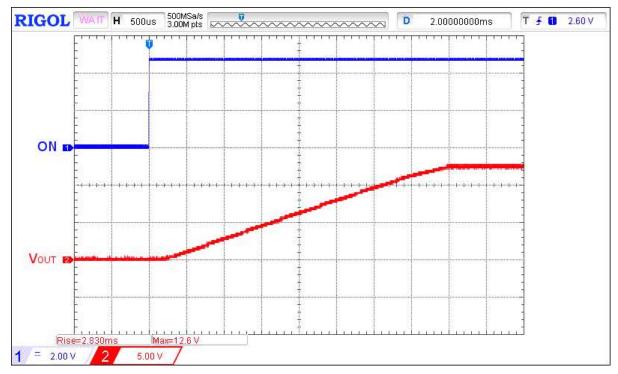


Figure 4. Typical Turn ON operation waveform for V<sub>IN</sub> = 12 V, C<sub>SLEW</sub> = 10 nF, C<sub>LOAD</sub> = 10  $\mu$ F, R<sub>LOAD</sub> = 100  $\Omega$ 

Datasheet	Revision 1.03	2-Feb-2022
CFR0011-120-01	Page 15 of 32	©2022 Renesas Electronics Corporation



A 12 V, 15 m $\Omega,$  4 A Load Switch with  $V_{IN}$  Lockout Select and Power Good Output

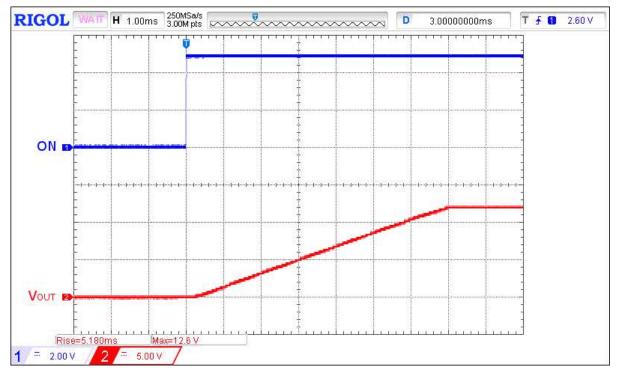


Figure 5. Typical Turn ON operation waveform for V<sub>IN</sub> = 12 V, C<sub>SLEW</sub> = 18 nF, C<sub>LOAD</sub> = 10  $\mu$ F, R<sub>LOAD</sub> = 100  $\Omega$ 

#### **Typical Turn-off Waveforms**

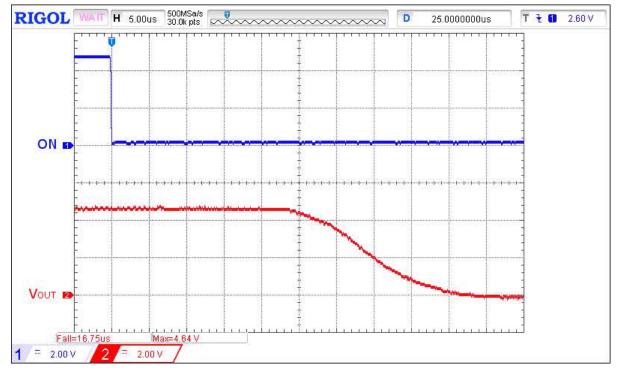


Figure 6. Typical Turn OFF operation waveform for V<sub>IN</sub> = 4.5 V, C<sub>SLEW</sub> = 10 nF, no C<sub>LOAD</sub> , R<sub>LOAD</sub> = 100  $\Omega$ 

Datasheet	Revision 1.03	2-Feb-2022	
CFR0011-120-01	Page 16 of 32	©2022 Renesas Electronics Corporation	



A 12 V, 15 m $\Omega,$  4 A Load Switch with  $V_{IN}$  Lockout Select and Power Good Output

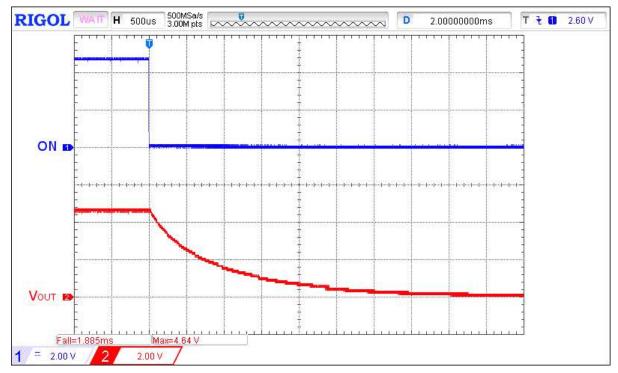


Figure 7. Typical Turn OFF operation waveform for V<sub>IN</sub> = 4.5 V, C<sub>SLEW</sub> = 10 nF, C<sub>LOAD</sub> = 10  $\mu$ F, R<sub>LOAD</sub> = 100  $\Omega$ 

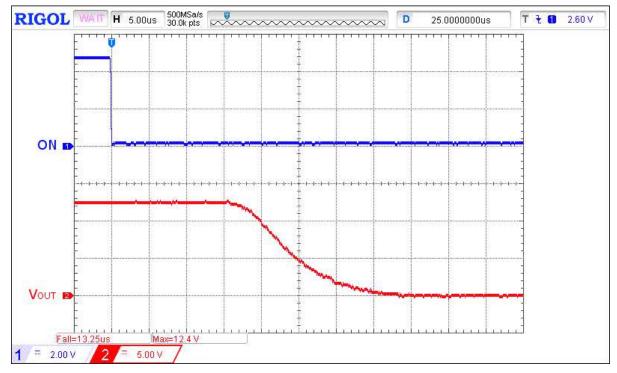


Figure 8. Typical Turn OFF operation waveform for V<sub>IN</sub> = 12 V, C<sub>SLEW</sub> = 10 nF, no C<sub>LOAD</sub> , R<sub>LOAD</sub> = 100 Ω

Datasheet	Revision 1.03	2-Feb-2022
CFR0011-120-01	Page 17 of 32	©2022 Renesas Electronics Corporation



A 12 V, 15 m $\Omega,$  4 A Load Switch with  $V_{IN}$  Lockout Select and Power Good Output

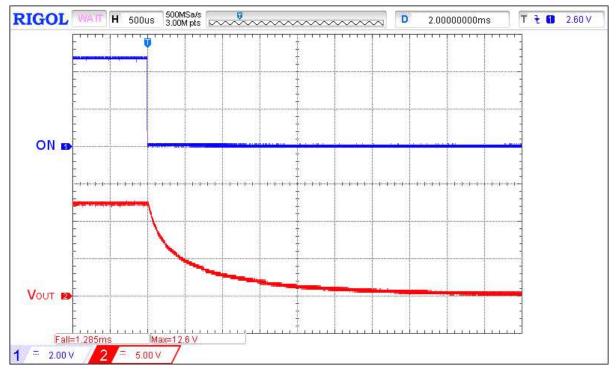


Figure 9. Typical Turn OFF operation waveform for V<sub>IN</sub> = 12 V, C<sub>SLEW</sub> = 10 nF, C<sub>LOAD</sub> = 10  $\mu$ F, R<sub>LOAD</sub> = 100  $\Omega$ 

#### **Typical ACL Operation Waveforms**

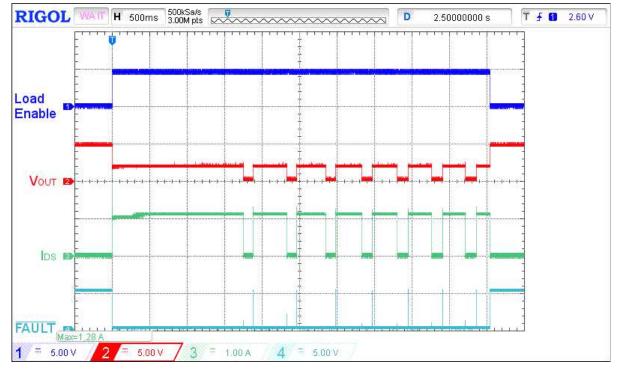


Figure 10. Typical ACL operation waveform for V<sub>IN</sub> = 4.5 V, C<sub>LOAD</sub> = 10  $\mu$ F, I<sub>ACL</sub> = 1 A, R<sub>SET</sub> = 95.3 k $\Omega$ 

Datasheet	Revision 1.03	2-Feb-2022
CFR0011-120-01	Page 18 of 32	©2022 Renesas Electronics Corporation



A 12 V, 15 m $\Omega,$  4 A Load Switch with  $V_{IN}$  Lockout Select and Power Good Output

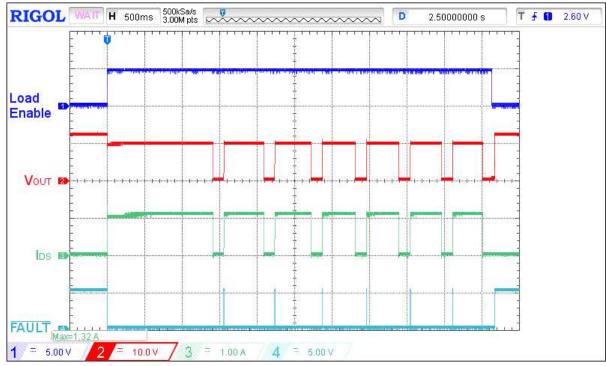


Figure 11. Typical ACL operation waveform for V<sub>IN</sub> = 12 V, C<sub>LOAD</sub> = 10  $\mu$ F, I<sub>ACL</sub> = 1 A, R<sub>SET</sub> = 95.3 k $\Omega$ 

#### **Typical FAULT Operation Waveforms**

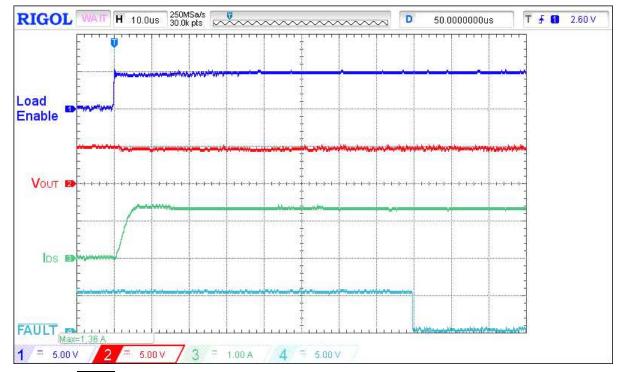


Figure 12. Typical FAULT assertion waveform for  $V_{IN}$  = 4.5 V,  $C_{LOAD}$  = 10 µF,  $I_{ACL}$  = 1 A,  $R_{SET}$  = 95.3 k $\Omega$ , switch on 3.3  $\Omega$  load

Datasheet	Revision 1.03	2-Feb-2022
CFR0011-120-01	Page 19 of 32	©2022 Renesas Electronics Corporation



A 12 V, 15 m $\Omega,$  4 A Load Switch with  $V_{IN}$  Lockout Select and Power Good Output

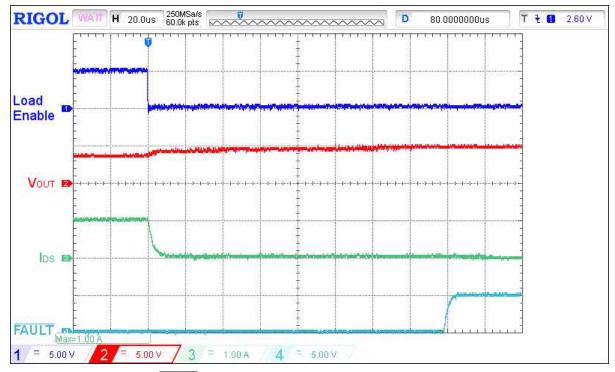


Figure 13. Typical FAULT de-assertion waveform for V<sub>IN</sub> = 4.5 V, C<sub>LOAD</sub> = 10  $\mu$ F, I<sub>ACL</sub> = 1 A, R<sub>SET</sub> = 95.3 k $\Omega$ , switch out 3.3  $\Omega$  load

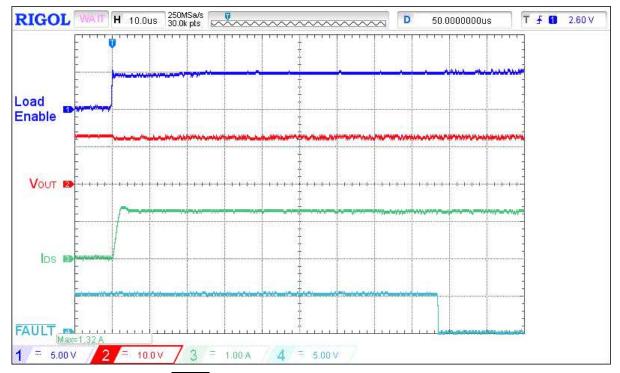


Figure 14. Typical FAULT assertion waveform for V<sub>IN</sub> = 12 V, C<sub>LOAD</sub> = 10  $\mu$ F, I<sub>ACL</sub> = 1 A, R<sub>SET</sub> = 95.3 k $\Omega$ , switch on 10  $\Omega$  load

Datasheet	Revision 1.03	2-Feb-2022
CFR0011-120-01	Page 20 of 32	©2022 Renesas Electronics Corporation



A 12 V, 15 mΩ, 4 A Load Switch with VIN Lockout Select and Power Good Output

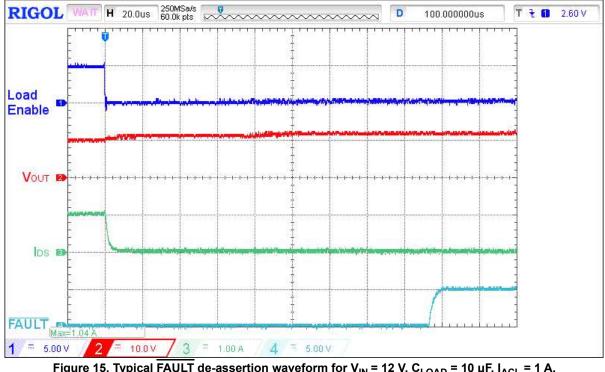
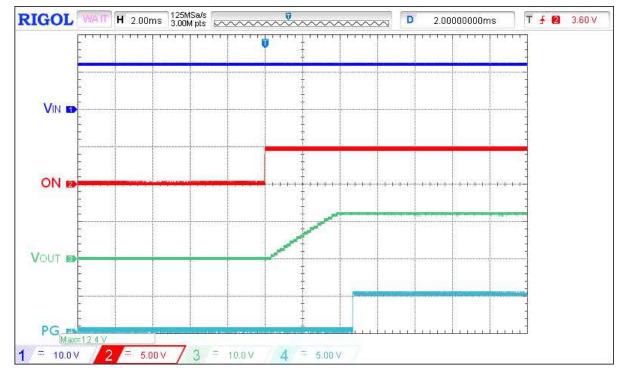


Figure 15. Typical FAULT de-assertion waveform for V<sub>IN</sub> = 12 V, C<sub>LOAD</sub> = 10  $\mu$ F, I<sub>ACL</sub> = 1 A, R<sub>SET</sub> = 95.3 k $\Omega$ , switch out 10  $\Omega$  load



## **Typical Power Good Waveform**

Figure 16. Typical Power Good operation waveform for  $V_{IN}$  = 12 V,  $C_{LOAD}$  = 10  $\mu$ F, no  $R_{LOAD}$ 

Datasheet	Revision 1.03	2-Feb-2022
CFR0011-120-01	Page 21 of 32	©2022 Renesas Electronics Corporation



A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### Typical SOA Waveforms

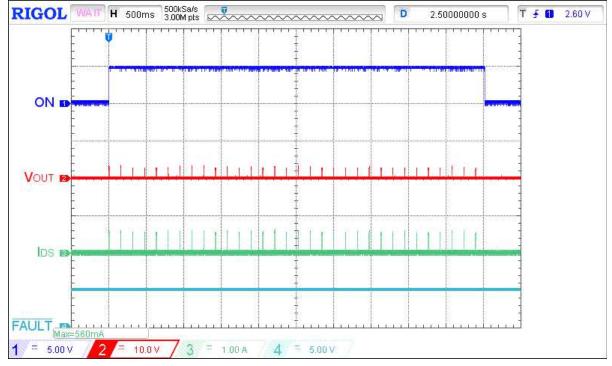


Figure 17. Typical SOA waveform during power up under heavy load for V<sub>IN</sub> = 12 V,  $C_{LOAD}$  = 10 µF,  $R_{SET}$  = 30.1 k $\Omega$ ,  $R_{LOAD}$  = 5  $\Omega$ 

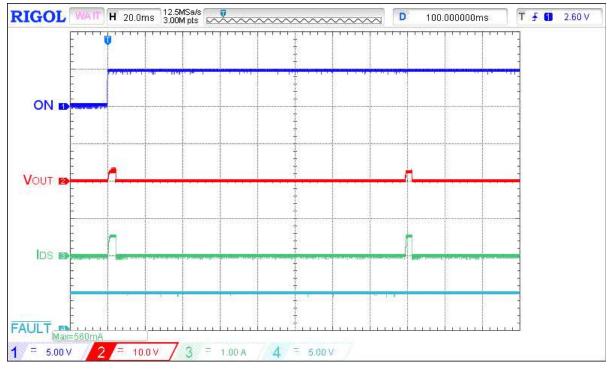


Figure 18. Extended typical SOA waveform during power up under heavy load for V<sub>IN</sub> = 12 V,  $C_{LOAD} = 10 \ \mu$ F,  $R_{SET} = 30.1 \ k\Omega$ ,  $R_{LOAD} = 5 \ \Omega$ 

Datasheet	Revision 1.03	2-Feb-2022

## A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### **Applications Information**

#### High Voltage GreenFET Safe Operating Area Explained

Renesas's High Voltage GreenFET load switches incorporate a number of internal protection features that prevents them from damaging themselves or any other circuit or subcircuit downstream of them. One particular protection feature is their Safe Operation Area (SOA) protection. SOA protection is automatically activated under overpower and, in some cases, under overcurrent conditions. Overpower SOA is activated if package power dissipation exceeds an internal 5 W threshold longer than 2.5 ms. High Voltage GreenFET devices will quickly switch off (open circuit) upon overpower detection and automatically resume (close) nominal operation once overpower condition no longer exists.

One of the possible ways to have an overpower condition trigger SOA protection is when High Voltage GreenFET products are enabled into heavy output resistive loads and/or into large load capacitors. It is under these conditions to follow carefully the "Safe Start-up Loading" guidance in the Applications section of the datasheet. During an overcurrent condition, High Voltage GreenFET devices will try to limit the output current to the level set by the external R<sub>SET</sub> resistor. Limiting the output current, however, causes an increased voltage drop across the FET's channel because the FET's RDS<sub>ON</sub> increased as well. Since the FET's RDS<sub>ON</sub> is larger, package power dissipation also increases. If the resultant increase in package power dissipation is higher/equal than 5 W for longer than 2.5 ms, internal SOA protection will be triggered and the FET will open circuit (switch off). Every time SOA protection is triggered, all High Voltage GreenFET devices will automatically attempt to resume nominal operation after 160 ms.

#### Safe Start-up Condition

SLG59H1127V has built-in protection to prevent over-heating during start-up into a heavy load. Overloading the VOUT pin with a capacitor and a resistor may result in non-monotonic  $V_{OUT}$  ramping or repeated restarts (*Figure 17* and *Figure 18*). In general, under light loading on VOUT,  $V_{OUT}$  ramping can be controlled with  $C_{SLEW}$  value. The following equation serves as a guide:

$$C_{SLEW} = \frac{T_{RISE}}{V_{IN}} \times 4.9 \,\mu A \times \frac{20}{3}$$

where  $T_{RISE}$  = Total rise time from 10% V<sub>OUT</sub> to 90% V<sub>OUT</sub>  $V_{IN}$  = Input Voltage  $C_{SLEW}$  = Capacitor value for CAP pin

When capacitor and resistor loading on VOUT during start up, the following tables will ensure V<sub>OUT</sub> ramping is monotonic without triggering internal protection:

Safe Start-up Loading for V <sub>IN</sub> = 12 V (Monotonic Ramp)				
Slew Rate (V/ms) $C_{SLEW} (nF)^2$ $C_{LOAD} (\mu F)$ $R_{LOAD} (\Omega)$				
1	33.3	500	20	
2	16.7	250	20	
3	11.1	160	20	
4	8.3	120	20	
5	6.7	100	20	

Note 2: Select the closest-value tolerance capacitor.

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## A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### Setting the SLG59H1127V's Active Current Limit

R <sub>SET</sub> (kΩ)	Active Current Limit (A) <sup>3</sup>
91	1
45	2
30	3
18	5

Note 3: Active Current Limit accuracy is ±15% over voltage range and temperature range

#### Setting the SLG59H1127V's Input Overvoltage Lockout Threshold

As shown in the table below, SEL selects the  $V_{IN}$  overvoltage threshold at which the SLG59H1127V's internal state machine will turn OFF (open circuit) the power MOSFET if  $V_{IN}$  exceeds the selected threshold.

SEL	V <sub>IN(OVLO)</sub> (Typ)
0	14.4 V

With an activated SLG59H1127V (ON=HIGH) and at any time  $V_{IN}$  crosses the programmed  $V_{IN}$  overvoltage threshold, the state machine opens the load switch and asserts the FAULT pin within TFAULT<sub>LOW</sub>.

In applications with a deactivated or inactive SLG59H1127V ( $V_{IN} > V_{IN(UVLO)}$  and ON=LOW) and if the applied  $V_{IN}$  is higher than the programmed  $V_{IN(OVLO)}$  threshold, the SLG59H1127V's state machine will keep the load switch open circuited if the ON pin is toggled LOW-to-HIGH. In these cases, the FAULT pin will also be asserted within TFAULT<sub>LOW</sub> and will remain asserted until  $V_{IN}$  resumes nominal, steady-state operation.

In all cases, the SLG59H1127V's V<sub>IN</sub> undervoltage lockout threshold is fixed at V<sub>IN(UVLO)</sub>.

#### **Power Dissipation**

The junction temperature of the SLG59H1127V depends on different factors such as board layout, ambient temperature, and other environmental factors. The primary contributor to the increase in the junction temperature of the SLG59H1127V is the power dissipation of its power MOSFET. Its power dissipation and the junction temperature in nominal operating mode can be calculated using the following equations:

$$PD = RDS_{ON} \times I_{DS}^2$$

where:

PD = Power dissipation, in Watts (W) RDS<sub>ON</sub> = Power MOSFET ON resistance, in Ohms ( $\Omega$ ) I<sub>DS</sub> = MOSFET current, in Amps (A) and

$$T_J = PD \times \theta_{JA} + T_A$$

where:

 $T_J$  = Junction temperature, in Celsius degrees (°C)  $\theta_{JA}$  = Package thermal resistance, in Celsius degrees per Watt (°C/W)  $T_A$  = Ambient temperature, in Celsius degrees (°C)

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2-Feb-2022



## A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### **Power Dissipation (continued)**

In current-limit mode, the SLG59H1127V's power dissipation can be calculated by taking into account the voltage drop across the load switch ( $V_{IN} - V_{OUT}$ ) and the magnitude of the output current in current-limit mode ( $I_{ACL}$ ):

 $PD = (V_{IN}-V_{OUT}) \times I_{ACL} \text{ or}$  $PD = (V_{IN} - (R_{LOAD} \times I_{ACL})) \times I_{ACL}$ 

where:

 $\begin{array}{l} \mathsf{PD} = \mathsf{Power dissipation, in Watts} \left(\mathsf{W}\right) \\ \mathsf{V}_{\mathsf{IN}} = \mathsf{Input Voltage, in Volts} \left(\mathsf{V}\right) \\ \mathsf{R}_{\mathsf{LOAD}} = \mathsf{Load Resistance, in Ohms} \left(\Omega\right) \\ \mathsf{I}_{\mathsf{ACL}} = \mathsf{Output limited current, in Amps} \left(\mathsf{A}\right) \\ \mathsf{V}_{\mathsf{OUT}} = \mathsf{R}_{\mathsf{LOAD}} \times \mathsf{I}_{\mathsf{ACL}} \end{array}$ 

**Datasheet** 

**Revision 1.03** 

## A 12 V, 15 m $\Omega,$ 4 A Load Switch with $V_{\text{IN}}$ Lockout Select and Power Good Output

#### Layout Guidelines:

- 1. Since the VIN and VOUT pins dissipate most of the heat generated during high-load current operation, it is highly recommended to make power traces as short, direct, and wide as possible. A good practice is to make power traces with <u>absolute minimum</u> <u>widths</u> of 15 mils (0.381 mm) per Ampere. A representative layout, shown in Figure 19, illustrates proper techniques for heat to transfer as efficiently as possible out of the device;
- To minimize the effects of parasitic trace inductance on normal operation, it is recommended to connect input C<sub>IN</sub> and output C<sub>LOAD</sub> low-ESR capacitors as close as possible to the SLG59H1127V's VIN and VOUT pins;
- 3. The GND pin should be connected to system analog or power ground plane.
- 4. 2 oz. copper is recommended for high current operation.

#### SLG59H1127V Evaluation Board:

A High Voltage GreenFET Evaluation Board for SLG59H1127V is designed according to the statements above and is illustrated on Figure 19. Please note that evaluation board has D\_Sense and S\_Sense pads. They cannot carry high currents and dedicated only for RDS<sub>ON</sub> evaluation.

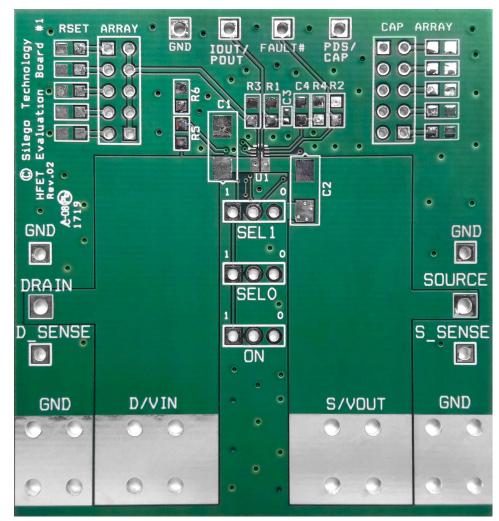


Figure 19. SLG59H1127V Evaluation Board

Datasheet	Revision 1.03	2-Feb-2022
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# A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

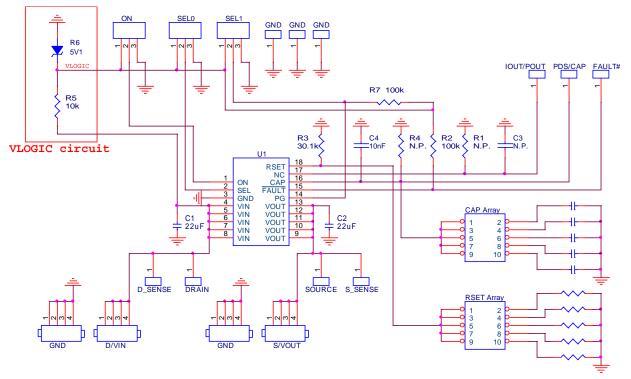


Figure 20. SLG59H1127V Evaluation Board Connection Circuit

#### **Basic Test Setup and Connections**

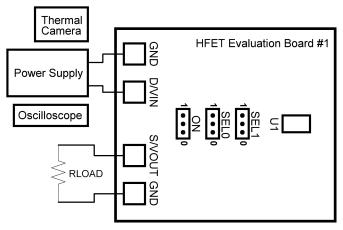


Figure 21. SLG59H1127V Evaluation Board Connection Circuit

#### **EVB** Configuration

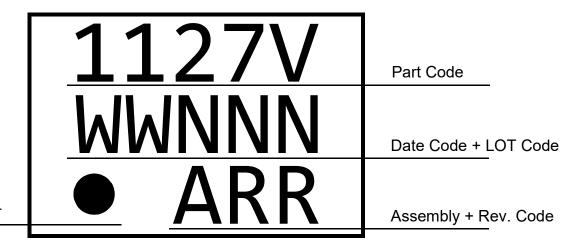
- 1. Set SEL0 to GND to configure OVLO;
- 2. Connect oscilloscope probes to D/VIN, S/VOUT, ON, etc.;
- 3. Turn on Power Supply and set desired  $V_{\text{IN}}$  from 4.5 V…12 V range;
- 4. Toggle the ON signal High or Low to observe SLG59H1127V operation.
- 5. Use central SEL1 header pin for PG monitor.

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A 12 V, 15 m $\Omega,$  4 A Load Switch with  $V_{IN}$  Lockout Select and Power Good Output

#### Package Top Marking System Definition



Pin 1 Identifier

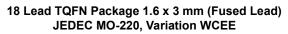
1127V - Part ID Field WW - Date Code Field<sup>1</sup> NNN - Lot Traceability Code Field<sup>1</sup> A - Assembly Site Code Field<sup>2</sup> RR - Part Revision Code Field<sup>2</sup>

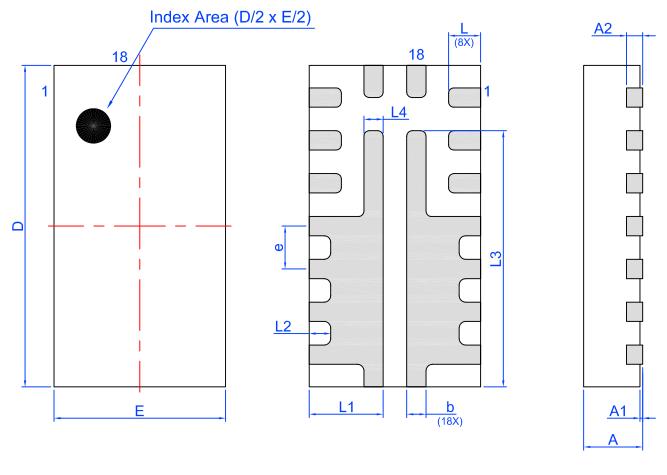
Note 1: Each character in code field can be alphanumeric A-Z and 0-9 Note 2: Character in code field can be alphabetic A-Z



A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### **Package Drawing and Dimensions**





## **Top View**

**BTM View** 

Side View

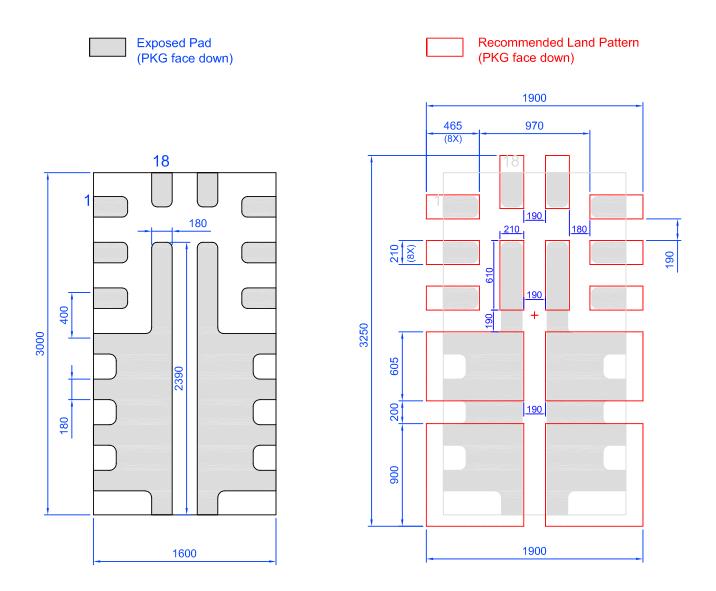
Unit<sup>.</sup> mm

Onic. min							
Symbol	Min	Nom.	Max	Symbol	Min	Nom.	Max
A	0.50	0.55	0.60	D	2.95	3.00	3.05
A1	0.005	-	0.05	E	1.55	1.60	1.65
A2	0.10	0.15	0.20	L	0.25	0.30	0.35
b	0.13	0.18	0.23	L1	0.64	0.69	0.74
е	0.40 BSC			L2	0.15	0.20	0.25
L3	2.34	2.39	2.44	L4	0.13	0.18	0.23



A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### SLG59H1127V 18-pin STQFN PCB Landing Pattern



Note: All dimensions shown in micrometers (µm)

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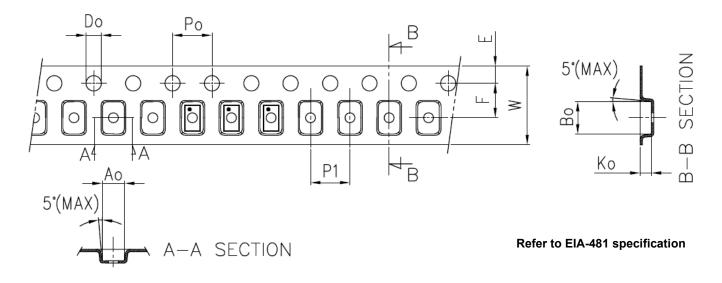
# A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### **Tape and Reel Specifications**

Baakaga	# of	Nominal	Max Units		Reel & Leader (min)		Trailer (min)		Tape F	Part	
Package Type	# of Pins	Package Size [mm]	per Reel	per Box	Hub Size [mm]	Pockets	Length [mm]	Pockets	Length [mm]	Width [mm]	Pitch [mm]
STQFN 18L 0.4P FC Green	18	1.6 x 3 x 0.55	3,000	3,000	178 / 60	100	400	100	400	8	4

#### **Carrier Tape Drawing and Dimensionss**

Package Type	PocketBTM Length	PocketBTM Width	Pocket Depth	Index Hole Pitch	Pocket Pitch	Index Hole Diameter	Index Hole to Tape Edge		Tape Width
	A0	В0	К0	P0	P1	D0	E	F	W
STQFN 18L 0.4P FC Green	1.78	3.18	0.76	4	4	1.5	1.75	3.5	8



#### **Recommended Reflow Soldering Profile**

Please see IPC/JEDEC J-STD-020: latest revision for reflow profile based on package volume of 2.64 mm<sup>3</sup> (nominal). More information can be found at www.jedec.org.



# A 12 V, 15 m $\Omega$ , 4 A Load Switch with V<sub>IN</sub> Lockout Select and Power Good Output

#### **Revision History**

Date	Version	Change
2/2/2022	1.03	Updated Company name and logo Added SOA Protection Threshold to Features Fixed typos Updated EVB image
12/12/2018	1.02	Updated style and formatting Updated Charts and Scopeshots Fixed typos
1/16/2018	1.01	Updated RDS <sub>ON</sub> vs V <sub>IN</sub> and Temp Chart
2/24/2017	1.00	Production Release

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